# 2SK3027 (Tentative)

## Silicon N-Channel Power F-MOS FET

### ■ Features

- Avalanche energy capacity guaranteed
- High-speed switching
- Low ON-resistance
- No secondary breakdown
- Low-voltage drive
- High electrostatic breakdown voltage

## ■ Applications

- Contactless relay
- Diving circuit for a solenoid
- Driving circuit for a motor
- Control equipment
- Switching power supply

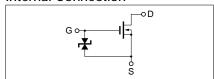
## ■ Absolute Maximum Ratings $(T_C = 25^{\circ}C)$

Parameter		Symbol	Ratings	Unit	
Drain to Source breakdown voltage		V <sub>DSS</sub>	60	V	
Gate to Source voltage		V <sub>GSS</sub>	±20	V	
Drain current	DC	$I_D$	±50	A	
	Pulse	$I_{DP}$	±100	A	
Avalanche energy capacity		EAS*	125	mJ	
Allowable power	$T_C = 25^{\circ}C$	D	60	W	
dissipation	Ta = 25°C	$P_{\rm D}$	2		
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature		$T_{stg}$	-55 to +150	°C	

<sup>\*</sup>  $L = 0.1 \text{mH}, I_L = 50 \text{A}, 1 \text{ pulse}$ 

# unit: mm 4.6±0.2 2.9±0.2 2.9±0.2 2.9±0.2 2.0±0.1 2.0±0.1 2.0±0.1 2.0±0.1 2.0±0.1 2.0±0.1 2.0±0.1 2.0±0.1 2.0±0.1 3: Source TO-220E Package (a)

## **Internal Connection**



## ■ Electrical Characteristics ( $T_C = 25$ °C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	$I_{DSS}$	$V_{DS} = 50V, V_{GS} = 0$			10	μA
Gate to Source leakage current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0$			±10	μΑ
Drain to Source breakdown voltage	$V_{DSS}$	$I_D = 1 \text{mA}, V_{GS} = 0$	60			V
Gate threshold voltage	$V_{th}$	$V_{DS} = 10V, I_D = 1mA$	1		2.5	V
Drain to Source ON-resistance	$R_{DS(on)1} \\$	$V_{GS} = 10V, I_D = 25A$		8	12	mΩ
	R <sub>DS(on)2</sub>	$V_{GS} = 4V, I_D = 25A$		11	17	mΩ
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10V, I_D = 25A$	25	49		S
Diode forward voltage	V <sub>DSF</sub>	$I_{DR} = 25A, V_{GS} = 0$			-1.2	V
Input capacitance (Common Source)	C <sub>iss</sub>			3600		pF
Output capacitance (Common Source)	Coss	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$		1250		pF
Reverse transfer capacitance (Common Source)	C <sub>rss</sub>			680		pF
Turn-on time (delay time)	t <sub>d(on)</sub>			20		ns
Rise time	t <sub>r</sub>	$V_{DD} = 30V, I_D = 25A$		65		ns
Fall time	$t_{\rm f}$	$V_{GS} = 10V, R_L = 1.2\Omega$		250		ns
Turn-off time (delay time)	t <sub>d(off)</sub>			960		ns
Thermal resistance between channel and case	R <sub>th(ch-c)</sub>				2.08	°C/W
Thermal resistance between channel and atmosphere	R <sub>th(ch-a)</sub>				62.5	°C/W

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